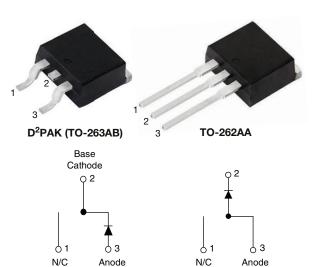
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VS-15ETX06S-M3, VS-15ETX06-1-M3

## **Vishay Semiconductors**

Hyperfast Rectifier, 15 A FRED Pt®



VS-15ETX06-1-M3

PRIMARY CHARACTERISTICS							
I <sub>F(AV)</sub>	15 A						
V <sub>R</sub>	600 V						
V <sub>F</sub> at I <sub>F</sub>	1.5 V						
t <sub>rr</sub> (typ.)	18 ns						
T <sub>J</sub> max.	175 °C						
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA						
Circuit configuration	Single						

VS-15ETX06S-M3

### FEATURES

- · Benchmark ultralow forward voltage drop
- Hyperfast recovery time
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 133 °C	15			
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	170	А		
Peak repetitive forward current	I <sub>FM</sub>		30			
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-				
	N	I <sub>F</sub> = 15 A	-	2.3	3.2	V			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	1.5	1.8				
	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	0.1	50				
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	40	300	μA			
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	20	-	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

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FREE



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## **Vishay Semiconductors**

DYNAMIC RECOVERY CHA	RACTERI	<b>STICS</b> (T <sub>C</sub> = 25 °C	unless otherwise s	pecified)			
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \ dI_F/dt = 100$	A/μs, V <sub>R</sub> = 30 V	-	18	22	
Poverse receiver time	+	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = 10$	0 Α/μs, V <sub>R</sub> = 30 V	-	20	32	20
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	22	-	115
		T <sub>J</sub> = 125 °C		-	52	-	
Pook receivery ourrent	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	2.4	-	•			
Peak recovery current		T <sub>J</sub> = 125 °C		-	5.1	-	A
	0	T <sub>J</sub> = 25 °C		-	TYP.     MAX.     UNITS       18     22		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	150	-	nc
Reverse recovery time	t <sub>rr</sub>		I <sub>F</sub> = 15 A	-	37	-	ns
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 800 A/µs	-	16	-	А
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	350	-	nC

THERMAL - MECHANICAL	SPECIFIC	ATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	1.0	1.3	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-	
Maight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davias		Case style D <sup>2</sup> PAK (TO-263AB)	15ETX06S			
Marking device		Case style TO-262AA		15ET	X06-1	



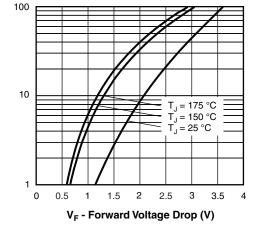
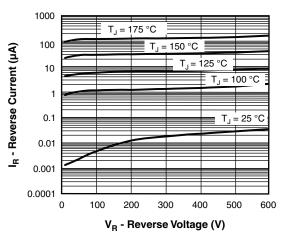
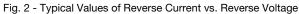


Fig. 1 - Typical Forward Voltage Drop Characteristics





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## VS-15ETX06S-M3, VS-15ETX06-1-M3

**Vishay Semiconductors** 

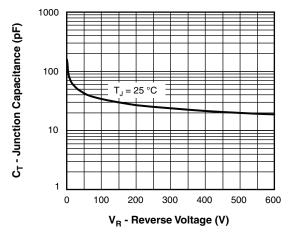


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

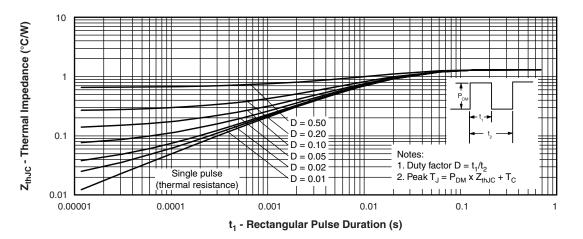


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

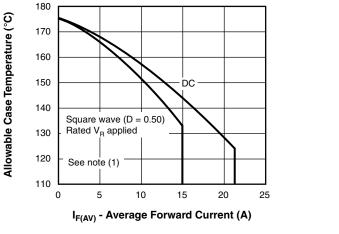


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

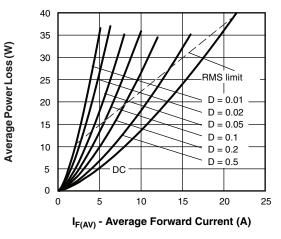


Fig. 6 - Forward Power Loss Characteristics

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# VS-15ETX06S-M3, VS-15ETX06-1-M3



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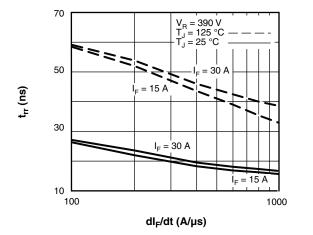


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
  - Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at ( $I_{F(AV)}/D$ ) (see fig. 6);  $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$

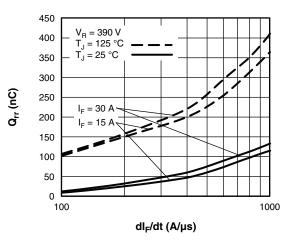


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

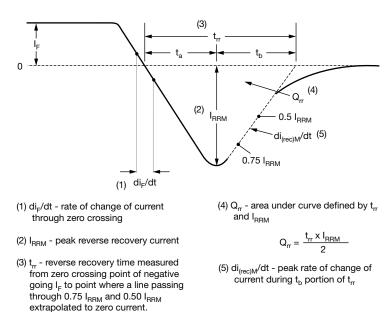
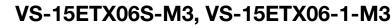


Fig. 9 - Reverse Recovery Waveform and Definitions



## **Vishay Semiconductors**

## **ORDERING INFORMATION TABLE**

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SHAY

			_	_			_		
Device code	VS-	15	E	т	X	06	S	TRL	-M3
	1	2	3	4	5	6	7	8	9
	1 - 2 - 3 -	Cur	nay Sen rent rati single c	ng (15 A	-	oduct			
	4 -		TO-220		•	63AB)			
	5 - 6 -		hyperfa tage rati		-	1			
	7 -		= D <sup>2</sup> PA						
		• -1	= TO-2	62AA					
	8 -	• N	one = tu	be (50 p	pieces)				
		• TI	RL = tap	e and re	eel (left	orientec	d, for D <sup>2</sup>	<sup>2</sup> PAK (T	O-263A
	9 -		RR = tap ironmer			it oriente	ed, for l	D <sup>2</sup> PAK (	(TO-263
		-M3	= halog	en-free	, RoHS-	complia	nt, and	termina	tions le

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-15ETX06S-M3	50	Antistatic plastic tubes				
VS-15ETX06STRR-M3	800	13" diameter plastic tape and reel				
VS-15ETX06STRL-M3	800	13" diameter plastic tape and reel				
VS-15ETX06-1-M3	50	Antistatic plastic tubes				

	LINKS TO RELAT	ED DOCUMENTS
Dimensions	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262	www.vishay.com/doc?96165
Part marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444
Fart marking information	TO-262	www.vishay.com/doc?95443
Packaging information		www.vishay.com/doc?96424

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**Vishay Semiconductors** 

D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	MILLIMETERS		INCHES		
STMBOL	MIN.	MAX.	MIN. MAX.		NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
	STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54	2.54 BSC		0.100 BSC	
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25	BSC	0.010	BSC	
	L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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Document Number: 96164

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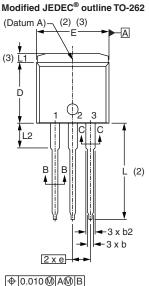
## **Outline Dimensions**

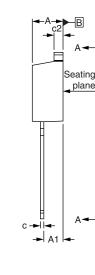


**Vishay Semiconductors** 

**TO-262AA** 

### **DIMENSIONS** in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CVMPOI	MILLIN	IETERS	INC	INCHES			
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
E	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	BSC	0.100 BSC				
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

 <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis and the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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